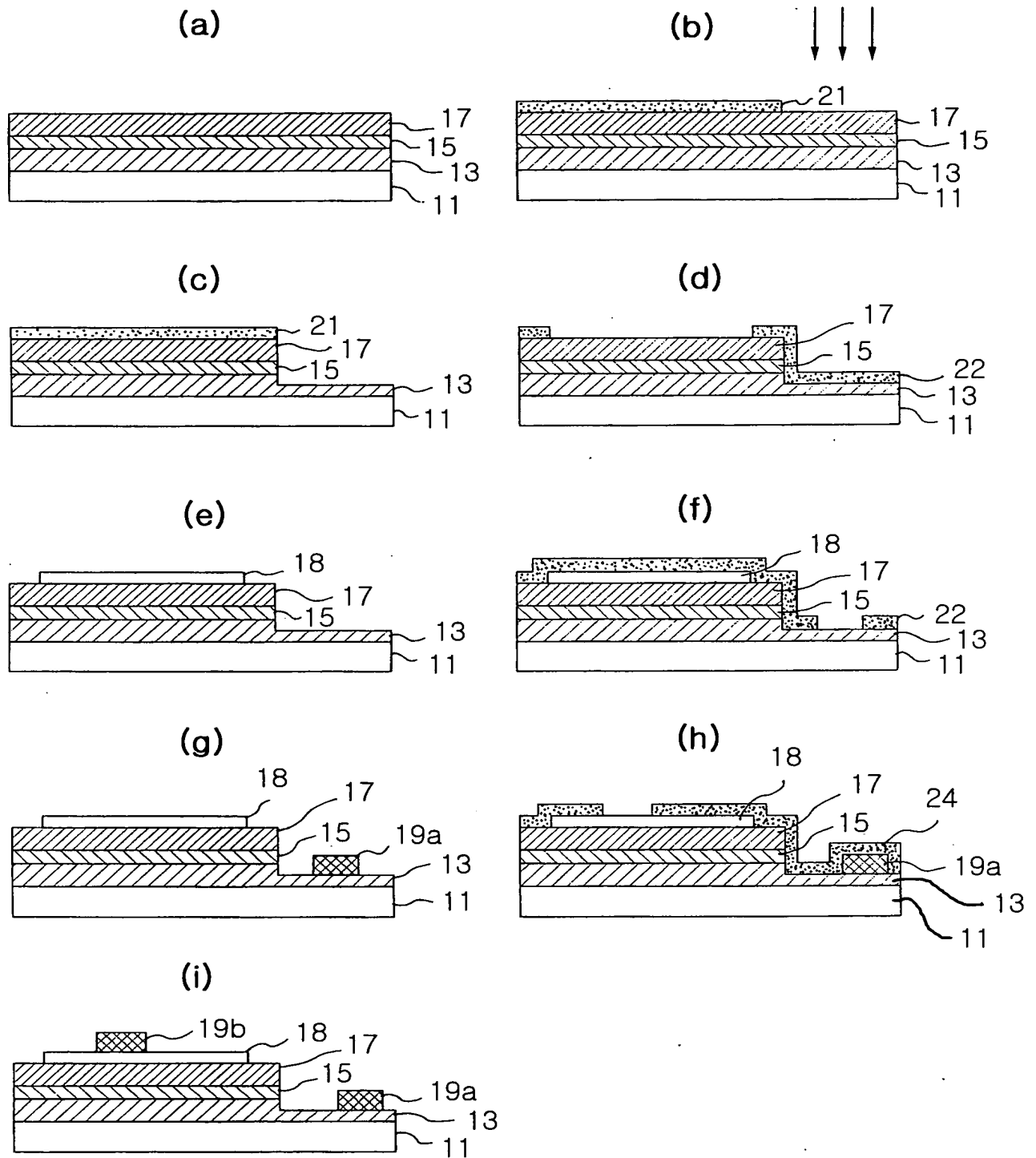


METHOD FOR MANUFACTURING GALLIUM NITRIDE-BASED SEMICONDUCTOR LIGHT  
EMITTING DEVICE

Inventor: Young Ho PARK  
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PRIOR ART

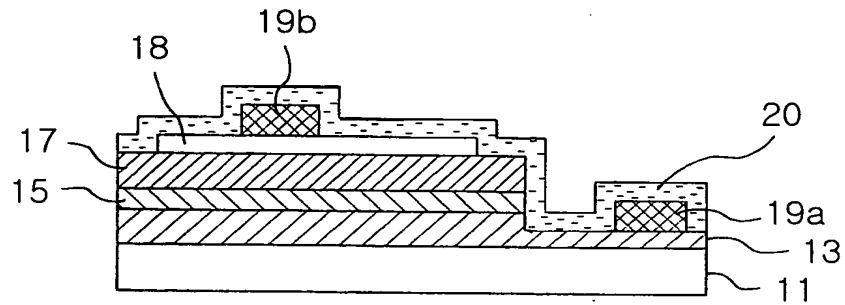
FIG. 1

METHOD FOR MANUFACTURING GALLIUM NITRIDE-BASED SEMICONDUCTOR LIGHT  
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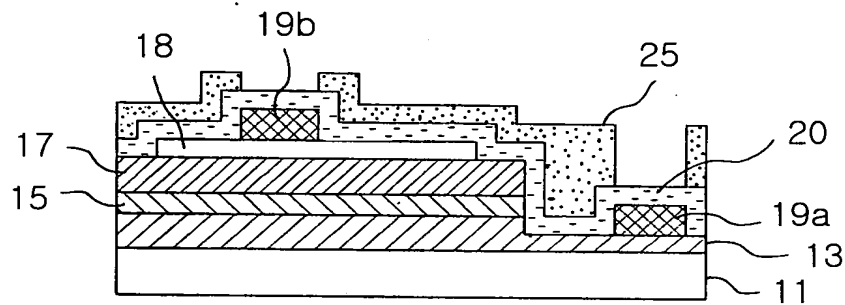
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(a)



(b)



(c)

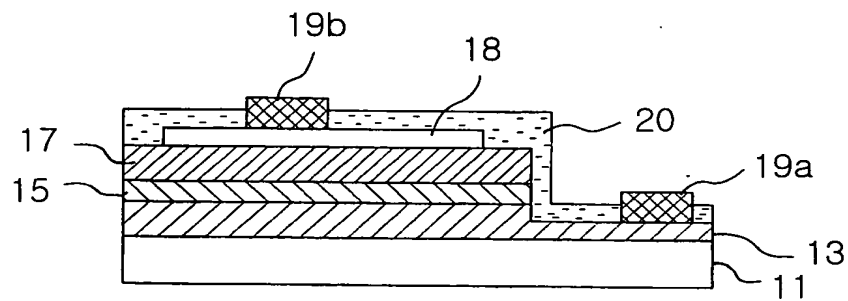


FIG. 2

METHOD FOR MANUFACTURING GALLIUM NITRIDE-BASED SEMICONDUCTOR LIGHT  
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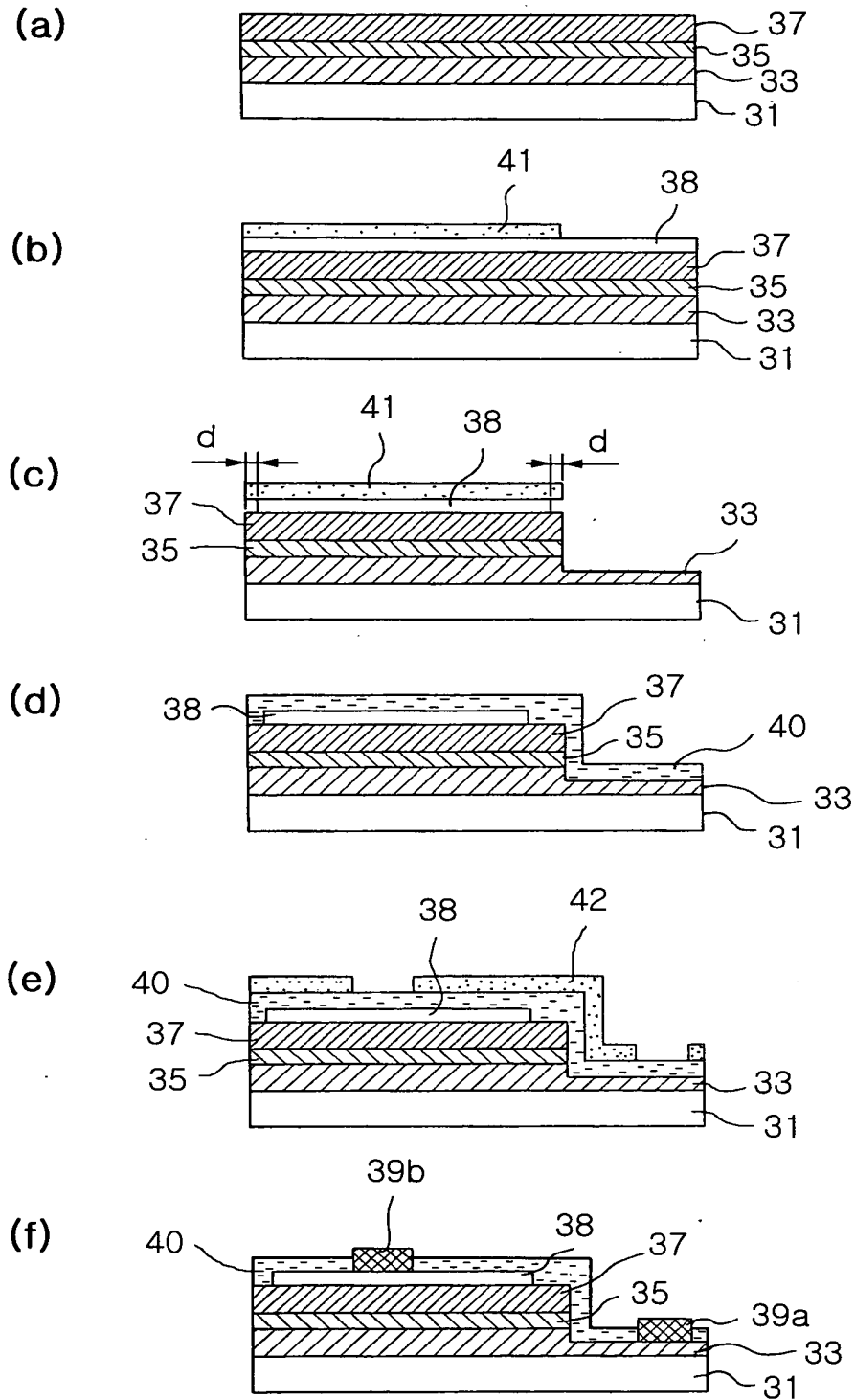


FIG. 3